NSN 5962-01-226-4337

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0.840 inches	
Body Width:	
Between 0.220 inches	and 0.310 inches
Body Height:	
0.185 inches	
Maximum Power Dis	sipation Rating:
739.0 milliwatts	
Operating Tempurate	ire Range:
-55.0/+125.0 degrees	celsius
Storage Tempurature	Range:
-65.0/+150.0 degrees	celsius
Features Provided:	
Hermetically sealed ar	d schottky and bipolar and programmable and monolithic
nclosure Material:	
Ceramic and glass	
nclosure Configurat	on:
Dual-in-line	
Output Logic Form:	
Transistor-transistor Ic	gic
nput Circuit Pattern	
10 input	
Case Outline Source	And Designator:
D-2 mil-m-38510	
Terminal Surface Tre	atment:
Solder	
Voltage Rating And 1	ype Per Characteristic:
7.0 volts power sourc	
Time Rating Per Cha	cteristic:
75.00 nanoseconds p	ropagation delay time, low to high level output and 75.00 nanoseconds propagation delay time, high to low level
output	
Memory Device Type	:
Rom	
Test Data Document	
96906-mil-std-883 sta	ndard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And C	
16 printed circuit	
Shelf Life:	
N/a	
Unit Of Measure:	
Demilitarization:	

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